



20V P-Channel MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-20	39 @ V _{GS} = -4.5V	-4.7	
	52 @ V _{GS} = -2.5V	-4.1	
	68 @ V _{GS} = -1.8V	-2.0	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

D° S G° S

Block Diagram

P-Channel MOSFET

Ordering Information

Part No.	Package	Packing
TSM2323CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denote for Green Product

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current, V _{GS} @ 4.5V	' .	I _D	-4.7	А	
Pulsed Drain Current, V _{GS} @ 4.5V		I _{DM}	-20	А	
Continuous Source Current (Diode Cor	nduction) ^{a,b}	Is	-1.0	А	
Maximum Power Dissipation	Ta = 25°C	5	1.25	W	
	Ta = 70°C	$ P_D$	0.8		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	120	°C/W

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature





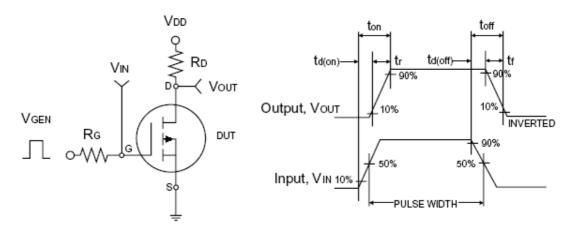


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250uA$	$V_{GS(TH)}$	-0.4		-1.0	V
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}	-		-1.0	uA
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
On-State Drain Current	V _{DS} ≤-5V, V _{GS} = -4.5V	$I_{D(ON)}$	-20			Α
	$V_{GS} = -4.5V$, $I_D = -4.7A$		1	31	39	
Drain-Source On-State Resistance	$V_{GS} = -2.5V$, $I_D = -4.1A$	R _{DS(ON)}	1	41	52	mΩ
	$V_{GS} = -1.8V$, $I_D = -2.0A$		1	54	68	
Forward Transconductance	$V_{DS} = -5V, I_{D} = -4.7A$	g _{fs}	1	16		S
Diode Forward Voltage	$I_S = -1.0A, V_{GS} = 0V$	V_{SD}		- 0.7	-1.2	V
Dynamic ^b		_		_		
Total Gate Charge	\/ 10\/ 17\	Q_g		12.5	19	
Gate-Source Charge	$V_{DS} = -10V, I_D = -4.7A,$ $V_{GS} = -4.5V$	Q_gs		1.7		nC
Gate-Drain Charge	V _{GS} = -4.5 V	Q_{gd}		3.3		
Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$	C_{iss}		1020		
Output Capacitance		C _{oss}	1	191		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}	1	140		
Switching ^{b,C}						
Turn-On Delay Time	$V_{DD} = -10V, R_{L} = 10\Omega,$ $I_{D} = -1A, V_{GEN} = -4.5V,$ $R_{G} = 6\Omega$	t _{d(on)}		25	40	
Turn-On Rise Time		t _r		43	65	20
Turn-Off Delay Time		t _{d(off)}		71	110	nS
Turn-Off Fall Time		t _f		48	75	

Notes:

- a. pulse test: PW ≤ 300µS, duty cycle ≤ 2%
- b. Guaranteed by design of component.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

Version: F15

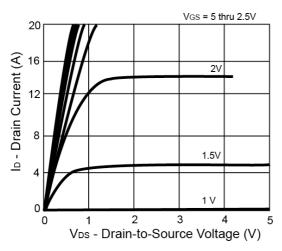




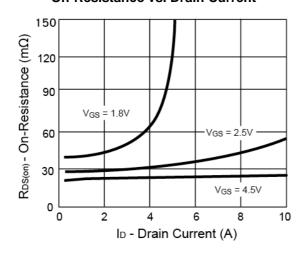


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

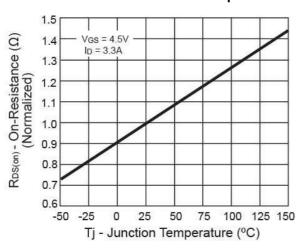
Output Characteristics



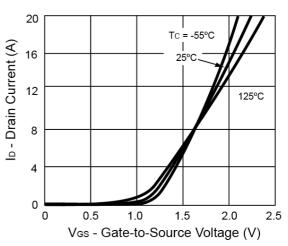
On-Resistance vs. Drain Current



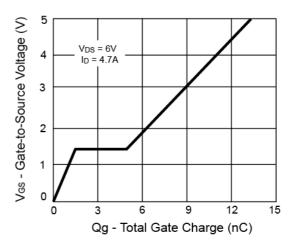
On-Resistance vs. Junction Temperature



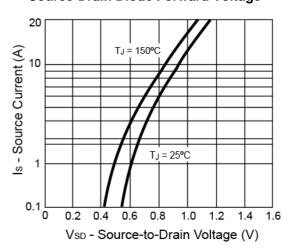
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



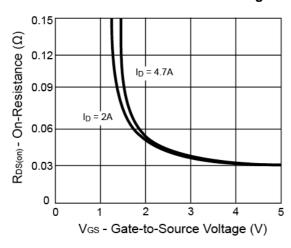




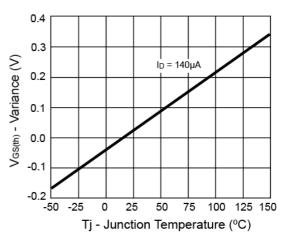


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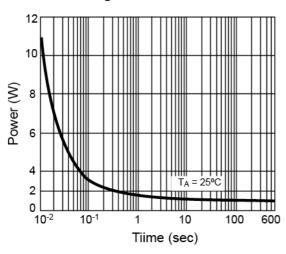
On-Resistance vs. Gate-Source Voltage



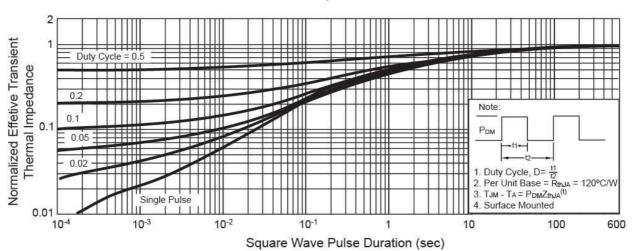
Threshold Voltage



Single Pulse Power



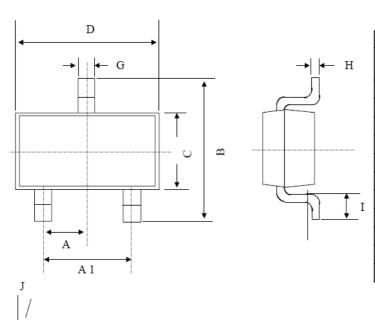
Normalized Thermal Transient Impedance, Junction-to-Ambient







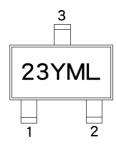
SOT-23 Mechanical Drawing



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SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
וווט	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037 BSC		
A1	1.9	BSC	0.074 BSC		
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Ш	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Η	0.10	0.20	0.004	0.008	
İ	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	

Marking Diagram



23 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



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